

isc Silicon NPN Power Transistor

2SD1408

DESCRIPTION

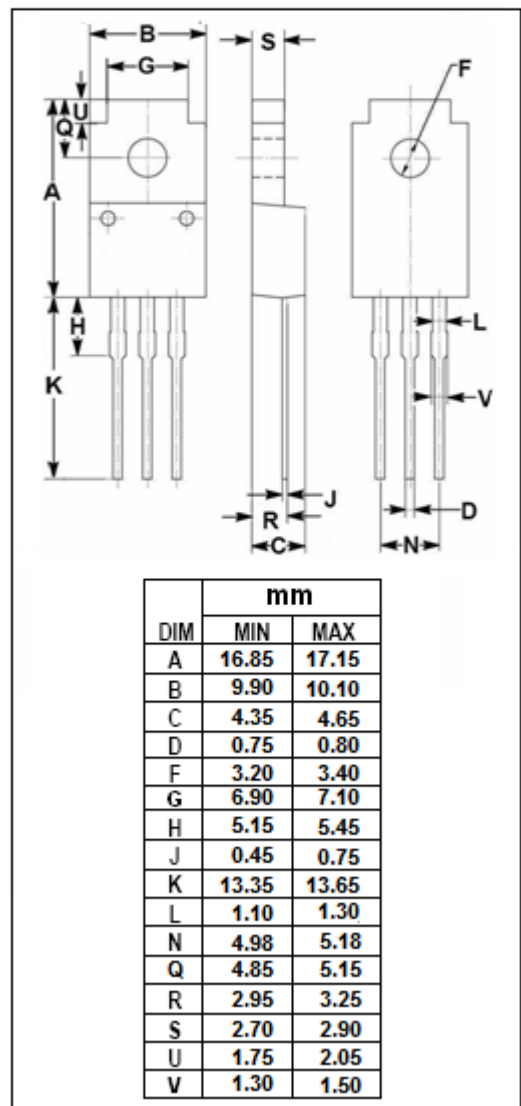
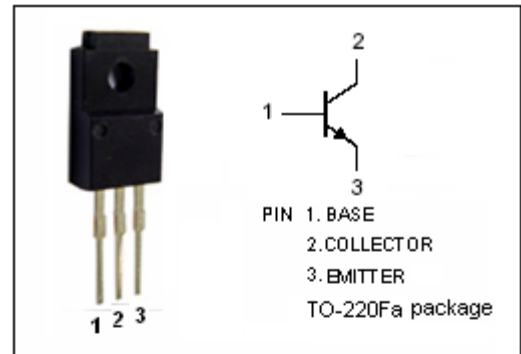
- Low Collector Saturation Voltage
: $V_{CE(sat)} = 1.5V(\text{Max}) @ I_C = 3A$
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 80V(\text{Min})$
- Complement to Type 2SB1017

APPLICATIONS

- Designed for power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	4	A
I_B	Base Current-Continuous	0.4	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	25	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon NPN Power Transistor**2SD1408****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=50\text{mA}; I_B=0$	80			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=0.3\text{A}$			1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=3\text{A}; V_{CE}=5\text{V}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=80\text{V}; I_E=0$			30	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			0.1	mA
h_{FE-1}	DC Current Gain	$I_C=0.5\text{A}; V_{CE}=5\text{V}$	40		240	
h_{FE-2}	DC Current Gain	$I_C=3\text{A}; V_{CE}=5\text{V}$	15			
C_{OB}	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{\text{test}}=1\text{MHz}$		90		pF
f_T	Current-Gain—Bandwidth Product	$I_C=0.5\text{A}; V_{CE}=5\text{V}$		8		MHz

◆ **h_{FE} classifications**

R	O	Y
40-80	70-140	120-240